

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C
30V	460m $Ω$ @ V _{GS} = 4.5 V	0.9A
301	560mΩ @ V _{GS} = 2.5V	0.7A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Portable Applications
- Power Management Functions

Features and Benefits

- 0.4mm Ultra Low Profile Package for Thin Application
- 0.6mm² Package Footprint, 10 times Smaller than SOT23
- Low V_{GS(th)}, can be driven directly from a battery
- Low R_{DS(on)}
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

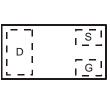
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 <a>@4
- Weight: 0.001 grams (Approximate)



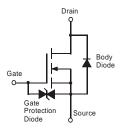




Bottom View



Top View



Equivalent Circuit

Ordering Information (Note 4)

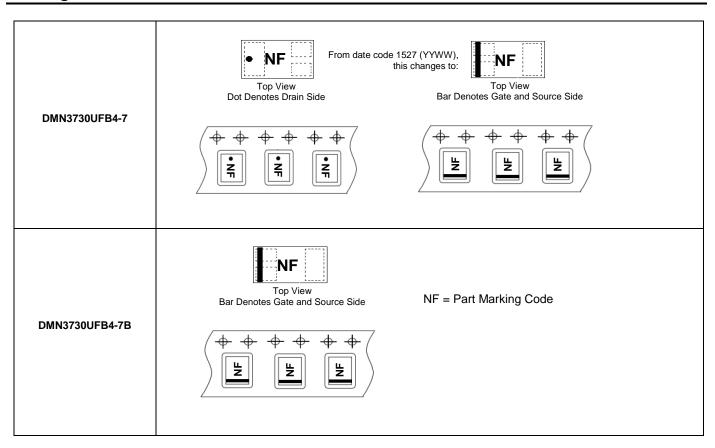
Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3730UFB4-7	NF	7	8	3,000
DMN3730UFB4-7B	NF	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±8	V
		(Note 6)	ID	0.91	А
Continuous Drain Current	$V_{GS} = 4.5V$	$T_A = +70^{\circ}C \text{ (Note 6)}$		0.73	
		(Note 5)		0.75	
Pulsed Drain Current		(Note 7)	I _{DM}	3	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Douger Discipation	(Note 6)	D	0.69	W	
Power Dissipation	(Note 5)	P _D	0.47		
Thermal Desistance Junction to Ambient	(Note 6)		180	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ hetaJA}$	258	C/VV	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes: 5. For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.

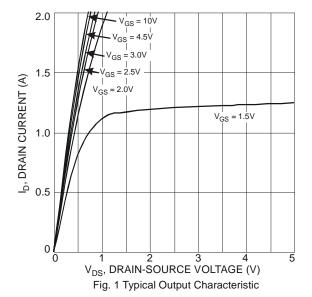
- 6. Same as note 4, except the device measured at $t \le 10$ seconds.
- 7. Same as note 4, except the device is pulsed at duty cycle of 1% for a pulse width of 10µs.

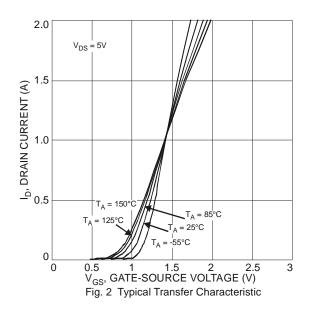


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

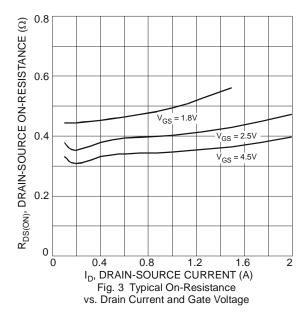
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	_	V	$V_{GS} = 0V$, $I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	1	1	1	μA	$V_{DS} = 30V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	3	μA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	0.45	_	0.95	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		_	_	460		$V_{GS} = 4.5V, I_D = 200mA$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	_	-	560	mΩ	$V_{GS} = 2.5V, I_D = 100mA$	
		_	_	730		$V_{GS} = 1.8V, I_D = 75mA$	
Forward Transfer Admittance	Y _{fs}	40	_	_	mS	$V_{DS} = 3V, I_{D} = 10mA$	
Diode Forward Voltage (Note 8)	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	1	64.3	_	pF		
Output Capacitance	Coss	1	6.1	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		4.5	_	pF	1 - 1.011112	
Gate Resistance	Rg	1	70	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	1.6	_	nC	451414	
Gate-Source Charge	Q_{gs}	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 1A$	
Gate-Drain Charge	Q_{gd}	_	0.2	_	nC		
Turn-On Delay Time	t _{D(on)}	_	3.5	_	ns	$V_{DS} = 10V, I_{D} = 1A$ $V_{GS} = 10V, R_{G} = 6\Omega$	
Turn-On Rise Time	t _r	_	2.8	_	ns		
Turn-Off Delay Time	t _{D(off)}	_	38	_	ns		
Turn-Off Fall Time	t _f	1	13	_	ns		

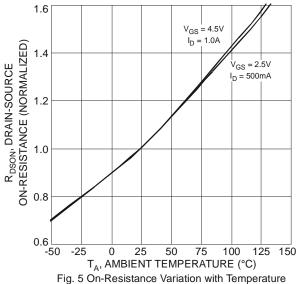
Notes: 8. Measured under pulsed conditions to minimize self-heating effect. Pulse width \leq 300 μ s; duty cycle \leq 2% 9. For design aid only, not subject to production testing.











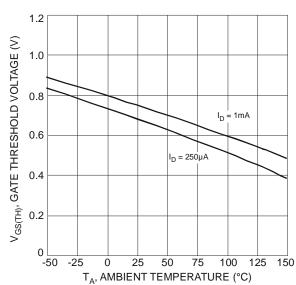


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

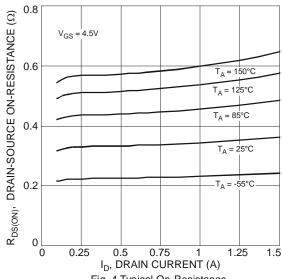


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

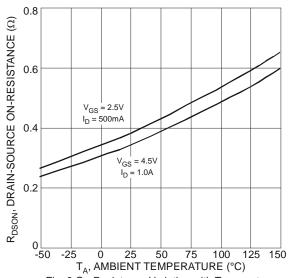


Fig. 6 On-Resistance Variation with Temperature

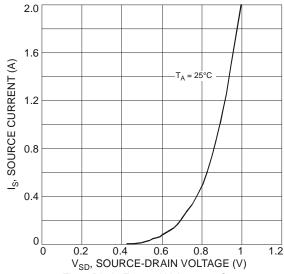
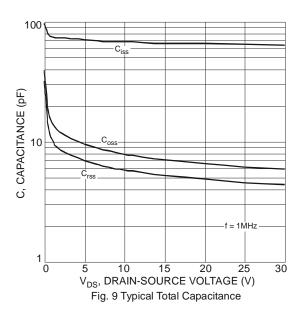
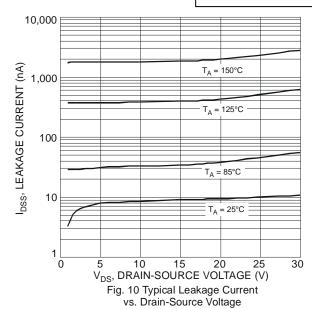
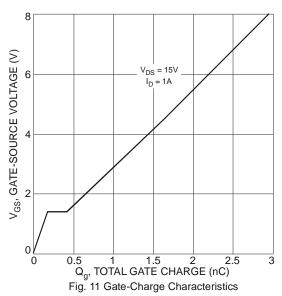


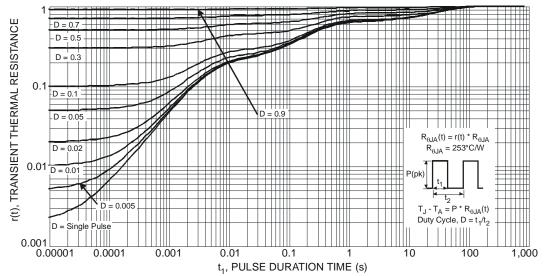
Fig. 8 Diode Forward Voltage vs. Current







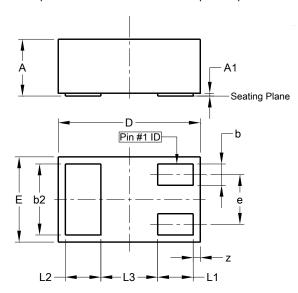






Package Outline Dimensions

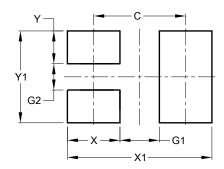
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40			
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

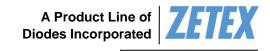
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Υ	0.25
Y1	0.70





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